

67C4033

First-In First-Out (FIFO)
64x5 Memory 10/15 MHz (Cascadable) CMOS

T-46-35

Advanced
Micro
Devices

DISTINCTIVE CHARACTERISTICS

- Zero standby power
- High-speed 15-MHz shift-in/shift-out rates
- Very low active power consumption
- TTL-compatible inputs and outputs
- Readily expandable in word width and depth
- Half-Full and Almost-Full/Empty status flags
- RAM-based architecture for short fall-through delay
- Full CMOS 8-transistor cell for maximum noise immunity
- Asynchronous operation
- Output enable

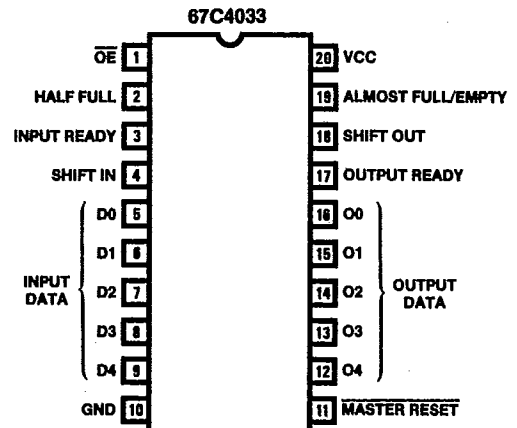
GENERAL DESCRIPTION

The 67C4033 device is a high-performance CMOS RAM-based First-In First-Out (FIFO) buffer product organized as 64 words by 5 bits wide. This device uses Monolithic Memories' latest CMOS process technology and meets the demands for high-speed, low-power operation. By utilizing an on-chip, dual-port RAM, a very short fall-through time is realized, thus improving overall system performance. By using Read and Write pointers for addressing each memory location, the data can propagate to the outputs in much less time than in traditional register-based FIFOs. These FIFOs are easily integrated into many applications and perform particularly well for high-speed disk controllers, graphics, and communication network systems. The 550 μ watt standby power specification of this device makes it ideal for ultra-low-power and battery-powered systems.

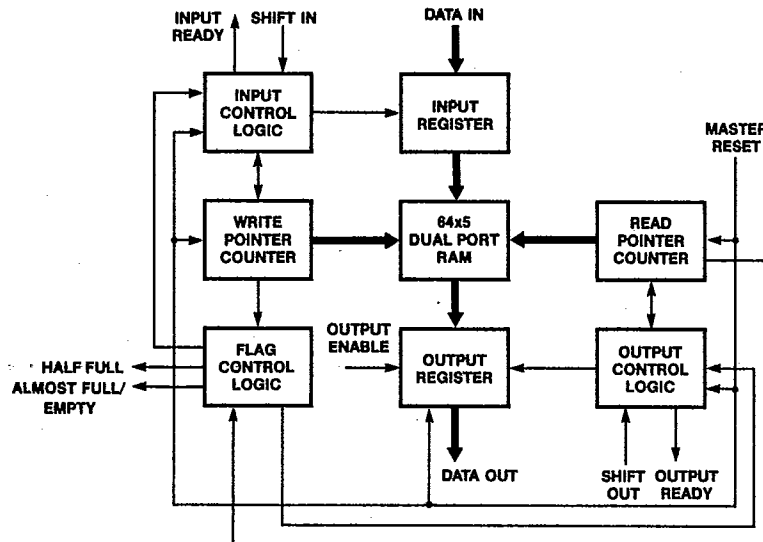
ORDERING INFORMATION

Part Number	Package	Temp	Description
67C4033-10	CD 020, PD 020, PL 020	Com	10 MHz in/out
67C4033-15	CD 020, PD 020, PL 020	Com	15 MHz in/out

CONNECTION DIAGRAMS



BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

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Supply voltage V_{CC}	-0.5 V to 7 V
Input voltage	-1.5 V to 7 V
Off-state output voltage	-0.5 V to $V_{CC} + 0.5$ V
Storage temperature	-65°C to +150°C
Power dissipation	1.0 W
Latch-up trigger current, all outputs	140 mA

OPERATING RANGES Over Temperature Range

SYMBOL	PARAMETER	FIGURE	67C4033-10		67C4033-15		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		4.5	5.5	4.5	5.5	V
T_A	Operating free-air temperature		0	70	0	70	°C
f_{IN}	Shift In rate	1		10		15	MHz
t_{SIH}	Shift in HIGH time	1,B	14		14		ns
t_{SIL}	Shift in LOW time	1	25		25		ns
t_{IDS}	Input data setup to SI (Shift In)	1	0		0		ns
t_{IDH}	Input data hold time from SI (Shift In)	1	40		40		ns
t_{RIDS}	Input data setup to IR (Input Ready)	3	0		0		ns
t_{RIDH}	Input data hold time from IR (Input Ready)	3	30		30		ns
f_{OUT}	Shift Out rate	4		10		15	MHz
t_{SOH}	Shift Out HIGH time	4,B	24		21		ns
t_{SOL}	Shift Out LOW time	4	25		25		ns
t_{MRW}^*	Master Reset pulse	8	35		35		ns
t_{MRS}	Master Reset to SI	8	65		65		ns

* See AC test and high-speed application note.

DC CHARACTERISTICS Over Operating Conditions

SYMBOL	PARAMETER	TEST CONDITION	67C4033-10		67C4033-15		UNIT
			MIN	MAX	MIN	MAX	
V_{IL}^*	Low-level input voltage			0.8		0.8	V
V_{IH}^*	High-level input voltage		2		2		V
I_{IN}	Input current	$V_{CC} = \text{MAX}$ $GND < V_{IN} < V_{CC}$	-1	1	-1	1	μA
I_{OZ}	Off-state output current	$V_{CC} = \text{MAX}$ $GND < V_{OUT} < V_{CC}$	-5	5	-5	5	μA
V_{OL}	Low-level output voltage	$V_{CC} = \text{MIN}$	$I_{OL} = 20 \mu\text{A}$	0.1		0.1	V
			$I_{OL} = 8 \text{ mA}$	0.4		0.4	
V_{OH}	High-level output voltage	$V_{CC} = \text{MIN}$	$I_{OH} = -20 \mu\text{A}$	$V_{CC} - 0.1$		$V_{CC} - 0.1$	V
			$I_{OH} = -4 \text{ mA}$	2.4		2.4	
I_{OS}^{**}	Output short-circuit current	$V_{CC} = \text{MAX}$ $V_O = 0 \text{ V}$	-90	-20	-90	-20	mA
I_{CC}	Standby supply current	$V_{CC} = \text{MAX}$ $V_{IH} = V_{CC}$ $V_{IL} = GND$		100		100	μA
	Operating supply current	$I_{OUT} = 0$ $V_{IH} = \text{MIN}, V_{IL} = \text{MAX}$ $f_{IN} = f_{OUT} = \text{MAX}$		35		45	mA

* These are absolute voltages with respect to GND (Pin 10) and include all overshoots due to system and/or tester noise.

** Not more than one output should be shorted at a time, and duration of the short circuit should not exceed one second.

SWITCHING CHARACTERISTICS Over Operating Conditions

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SYMBOL	PARAMETER	FIGURE	67C4033-10		67C4033-15		UNIT
			MIN	MAX	MIN	MAX	
t _{IRL} *	Shift In ↓ to Input Ready LOW	1		60		55	ns
t _{IRH} *	Shift In ↓ to Input Ready HIGH			50		50	ns
t _{ORL} *	Shift Out ↑ to Output Ready LOW	4		55		45	ns
t _{ORH} *	Shift Out ↓ to Output Ready HIGH			50		41	ns
t _{ODH}	Output Data Hold (previous word)		5		5		ns
t _{ODS}	Output Data Shift (next word)			35		30	ns
t _{PT}	Data throughput	3,6		100		90	ns
t _{MRORL}	Master Reset ↓ to Output Ready LOW	8		100		100	ns
t _{MRIRH}	Master Reset ↓ to Input Ready HIGH			100		100	ns
t _{MRO}	Master Reset ↓ to Outputs LOW			35		35	ns
t _{MRHFL}	Master Reset ↓ to Half-Full Flag LOW	9		100		100	ns
t _{MRAEH}	Master Reset ↓ to Almost Empty Flag HIGH			100		100	ns
t _{IPH}	Input ready pulse HIGH	3,B	19		16		ns
t _{OPH}	Output ready pulse HIGH	6,B	14		14		ns
t _{ORD}	Output ready ↓ to Data Valid	4		-3		-3	ns
t _{AEH}	Shift Out ↑ to AF/E HIGH	10		110		110	ns
t _{AEL}	Shift In ↓ to AF/E LOW			110		110	ns
t _{AFL}	Shift Out ↑ to AF/E LOW	11		110		110	ns
t _{AFH}	Shift In ↑ to AF/E HIGH			110		110	ns
t _{HFH}	Shift In ↑ to HF HIGH	12		110		110	ns
t _{HFL}	Shift Out ↓ to HF LOW			110		110	ns
t _{PHZ}	Output Disable Delay	A		25		25	ns
t _{PLZ}				25		25	ns
t _{PZL}	Output Enable Delay			30		30	ns
t _{PZH}				30		30	ns

* See timing diagram for explanation of parameters.

CAPACITANCES*

SYMBOL	PARAMETER	TEST CONDITION	67C4033-XX		UNIT
			MIN	MAX	
C _{IN}	Input capacitance	T _A = 25°C, f = 1 MHz V _{CC} = 4.5 V		10	pF
C _{OUT}	Output capacitance			7	pF

* Values not tested in production.

THREE-STATE TEST LOAD

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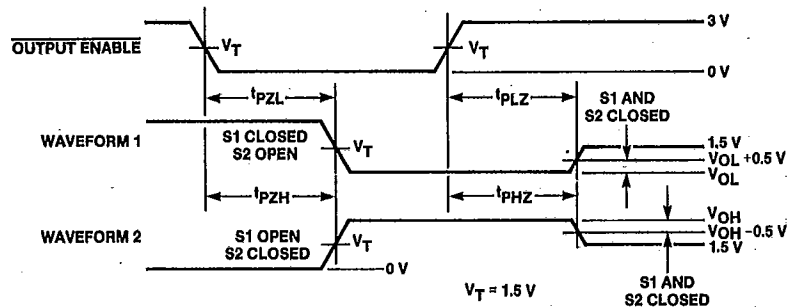
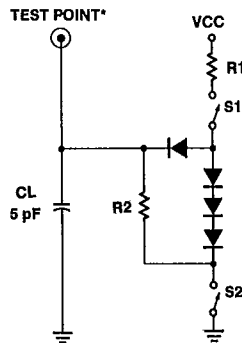
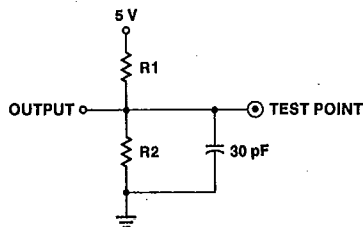


Figure A. Enable and Disable

Waveform 1 is for a data output with internal conditions such that the output is low except when disabled by the output control.

Waveform 2 is for a data output with internal conditions such that the output is high except when disabled by the output control.

STANDARD A.C. TEST LOAD



Input Pulse Amplitude = 3 V
 Input Rise and Fall Time (10%-90%) = 2.5 ns
 Measurements made at 1.5 V
 All Diodes are 1N916 or 1N3064

RESISTOR VALUES

I _{OL}	R1	R2
8 mA	600 Ω	1200 Ω

FUNCTIONAL DESCRIPTION

Data Input

The FIFO consists of a dual-port RAM and two ring counters for read and write. After power-up, the Master Reset should be pulsed LOW, which internally resets both the read and write counters. When the Input Ready (IR) is HIGH, the FIFO is ready to accept DATA from the D_x inputs. Data then present at the inputs is written into the first location of the RAM when Shift-In (SI) is brought HIGH. A SI HIGH signal causes the IR to go LOW. When the SI is brought LOW and the FIFO is not full, IR will go HIGH, indicating that more room is available. The write pointer now points to the next location in the RAM. If the memory is full, then the IR will remain LOW.

Data Output

Data is read from the O_x outputs. Just after the first shift-in, the first data word is available at the outputs, which is indicated by the Output Ready (OR) going HIGH. When the OR is HIGH, data may be shifted out by bringing the Shift-Out (SO) HIGH. A HIGH signal at SO causes the read pointer to point to the next location in the RAM, and also the OR to go LOW. Valid data is maintained while the SO is HIGH. When the SO is brought LOW, the OR goes HIGH, indicating the presence of new valid data. If the FIFO is emptied, OR stays LOW, and O_x remains as before, (i.e., data does not change if the FIFO is empty). A dual-port RAM inside the chip provides the capability of simultaneous and asynchronous writes (Shift-Ins) and reads (Shift-Outs).

AC TEST AND HIGH-SPEED APP. NOTES

Since the FIFO is a very-high-speed device, care must be exercised in the design of the hardware and the timing utilized within the design. Device grounding and decoupling is crucial to correct operation as the FIFO will respond to very small glitches due to long reflective lines, high capacitances and/or poor supply decoupling and grounding. Monolithic Memories recommends a monolithic ceramic capacitor of 0.1 μF directly between V_{CC} and GND with very short lead length. In addition, care must be exercised in how the timing is set up and how the parameters are measured. For example, since an AND gate function is associated with both the Shift-In-Input Ready combination, as well as the Shift-Out-Output Ready combination, timing measurements may be misleading; i.e., rising edge of the Shift-In pulse is not recognized until Input ready is HIGH. If Input Ready is not high due to (a) too high a frequency, or (b) FIFO being full or effected by Master Reset, the Shift-In activity will be ignored. This will affect the device from a functional standpoint, and will also cause the "effective" timing of Input Data Hold time (T_{IDH}) and the next activity of Input Ready (T_{IRL}) to be extended relative to Shift-In going HIGH. This same type of problem is also related to T_{IRH}, T_{ORL}, T_{ORH}, and the Status Flag timing as related to Shift-In and Shift-Out. For high-speed applications, proper grounding technique is essential.

HF AND AFE STATUS FLAGS

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The Half-Full (HF) will be high only when the net balance of words shifted into the FIFO exceeds the number of words shifted out by thirty-two or more (i.e., when the FIFO contains thirty-two or more words). The Almost-Full/Empty (AFE) flag will be HIGH when the FIFO contains fifty-six or more words or when the FIFO contains eight or fewer words (see Figures 9, 10, and 11).

Care should be exercised in using the status flags because they are capable of producing arbitrarily short pulses. For example, if

the FIFO contains thirty-one words, and SI and SO pulses are applied simultaneously, the HF flag may produce an arbitrarily short pulse, depending on the precise phase of SI and SO.

The flags will always settle to the correct state after the appropriate delay (e.g., T_{HFL} , T_{HFH} in this example). This property of the status flags will clearly be a function of the dynamic relation between SI and SO. Generally, the use of level-sensitive, rather than edge-sensitive, status detection circuits will alleviate this hazard.

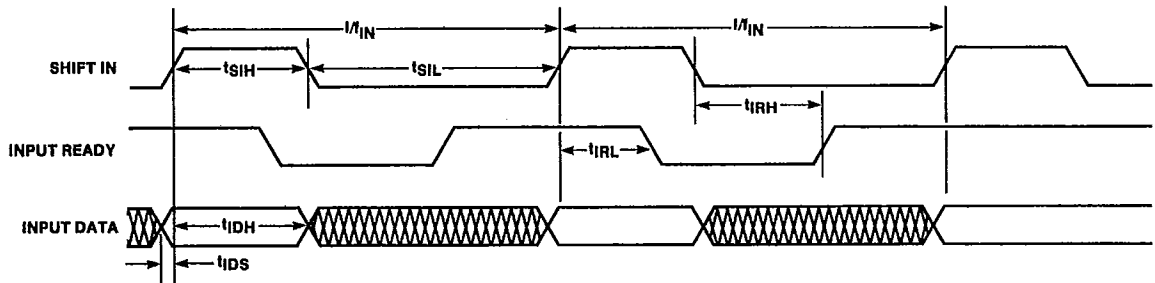


Figure 1. Input Timing

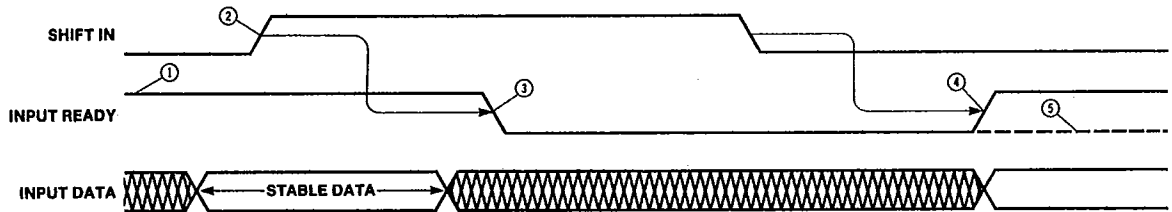


Figure 2. The Mechanism of Shifting Data into the FIFO

- ① Input Ready HIGH indicates space is available and a Shift-In pulse may be applied.
- ② Input Data is loaded into the first available memory location.
- ③ Input Ready goes LOW indicating this memory location is full.
- ④ Shift-In going LOW allows Input Ready to sense the status of the next memory location. The next memory location is empty as indicated by Input Ready HIGH.
- ⑤ If the FIFO is already full then the Input Ready remains low.

Note: Shift-In pulses applied while Input Ready is LOW will be ignored.

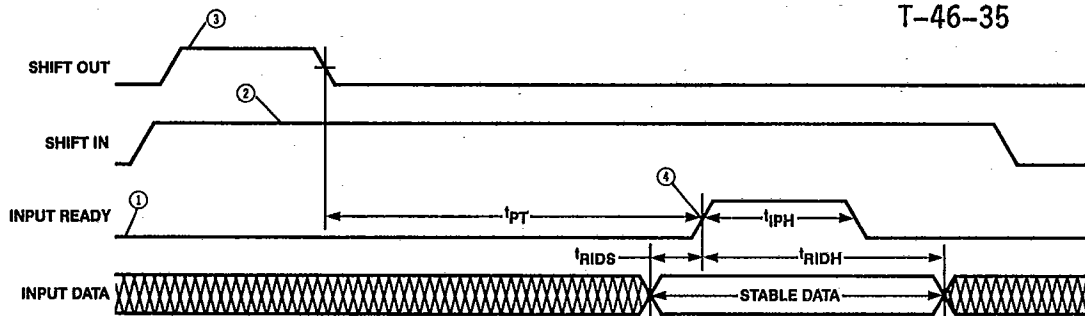


Figure 3. Data is Shifted In Whenever Shift In and Input Ready are Both HIGH

- ① FIFO is initially full.
- ② Shift In is held HIGH.
- ③ Shift Out pulse is applied. An empty location is detected by the internal pointers on the falling edge of SO.
- ④ As soon as Input Ready becomes HIGH the Input Data is loaded into this location.

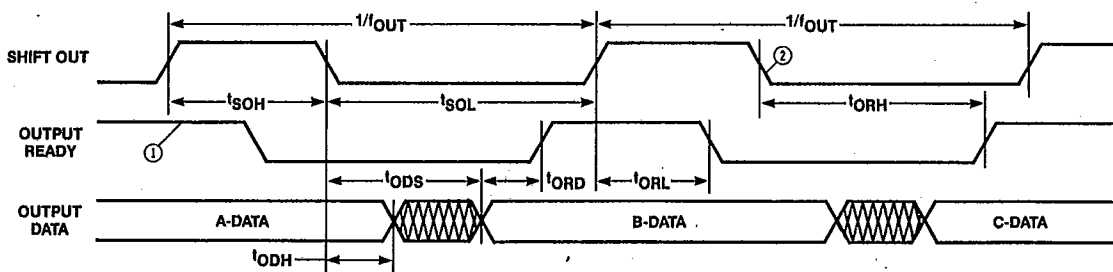


Figure 4. Output Timing

- ① The diagram assumes that the FIFO contains at least three words: A-Data (first input word), B-Data (second input word), and C-Data (third input word).
- ② Output data changes on the falling edge of SO after a valid Shift-Out Sequence, i.e., OR and SO are both high together.

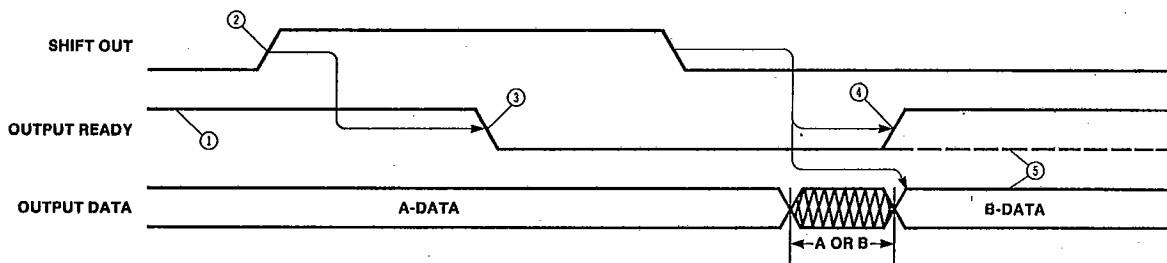


Figure 5. The Mechanism of Shifting Data Out of the FIFO

- ① Output Ready HIGH indicates that data is available and a Shift-Out pulse may be applied.
- ② Shift-Out goes HIGH causing B-Data (second input word) to advance to the output register. Output data remains as valid A-Data while Shift-Out is HIGH.
- ③ Output Ready goes LOW.
- ④ Shift-out goes LOW causing Output Ready to go HIGH and new data (B) to appear at the data outputs.
- ⑤ If the FIFO has only one word loaded (A-Data) then Output Ready stays LOW and the output data remains the same (A-Data).

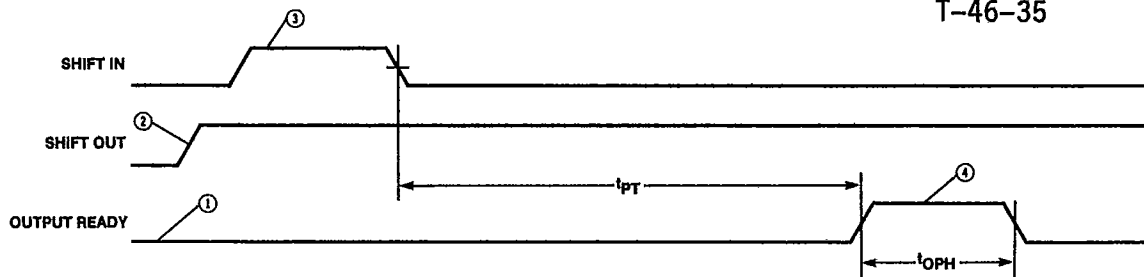


Figure 6. t_{PT} and t_{OPH} Specification

- ① FIFO is initially empty.
- ② Shift-Out is held HIGH.
- ③ Shift-In pulse applied. A full location is detected by the internal pointers on the falling edge of Shift-In
- ④ As soon as Output Ready becomes HIGH, the word is shifted out.

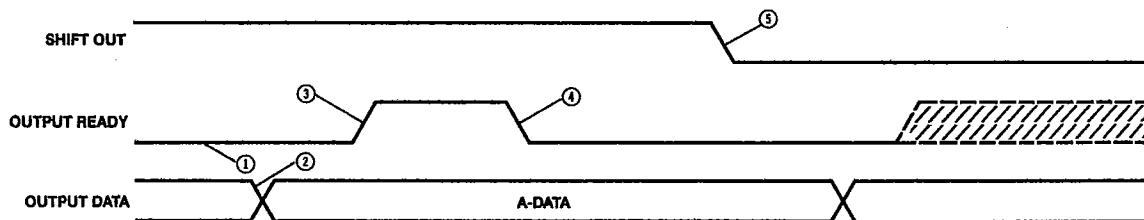


Figure 7. Data is Shifted Out Whenever Shift Out and Output Ready are Both HIGH

- ① The infernal logic does not detect the presence of any data in the FIFO.
- ② New data (A) arrives at the outputs.
- ③ Output Ready goes HIGH indicating arrival of the new data.
- ④ Since Shift Out is held HIGH, Output Ready goes immediately LOW.
- ⑤ As soon as Shift Out goes LOW the Output Data is subject to change. Output Ready will go HIGH or remain LOW depending on whether there are any additional upstream words in the FIFO.

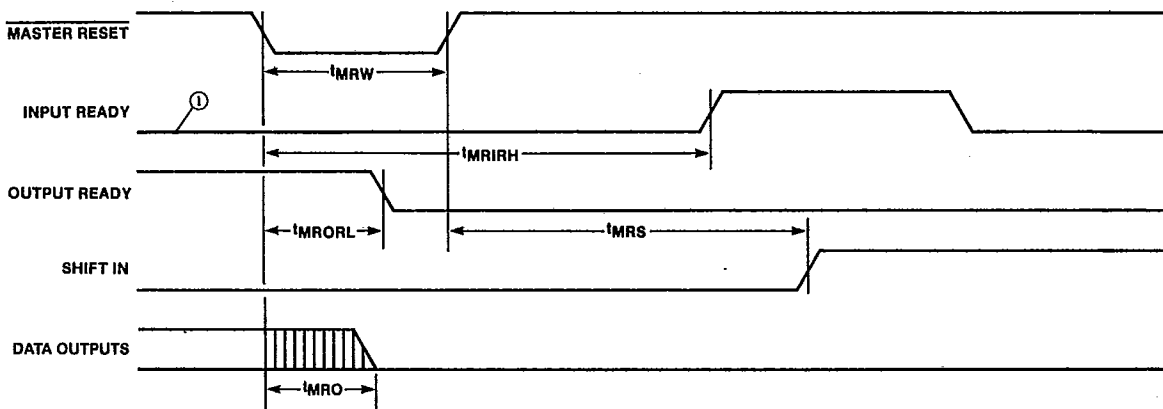


Figure 8. Master Reset Timing

- ① FIFO is initially full.

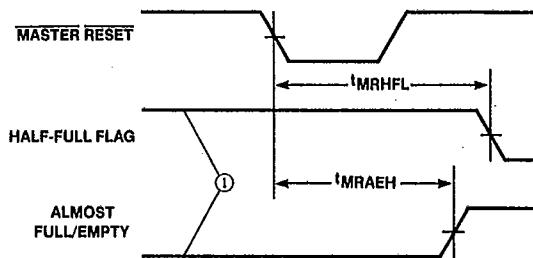


Figure 9. t_{MRHFL} , t_{MRAEH} Specifications

① FIFO Initially has between 32 and 56 words.

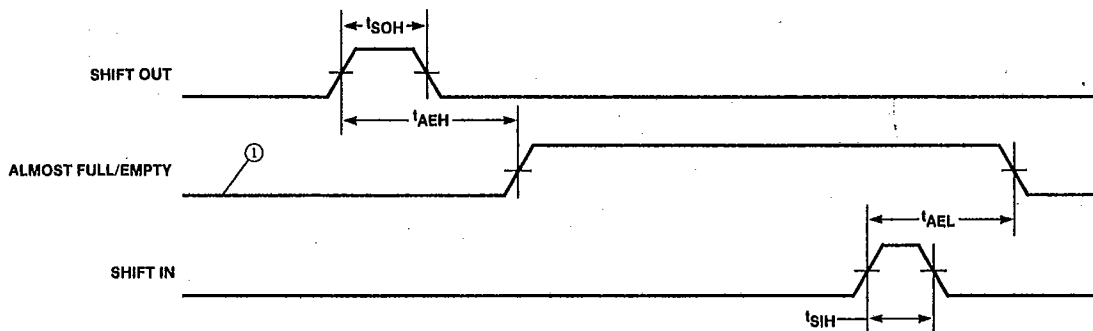


Figure 10. t_{AEH} , t_{AEL} Specifications

① FIFO contains 9 words (one more than almost empty).

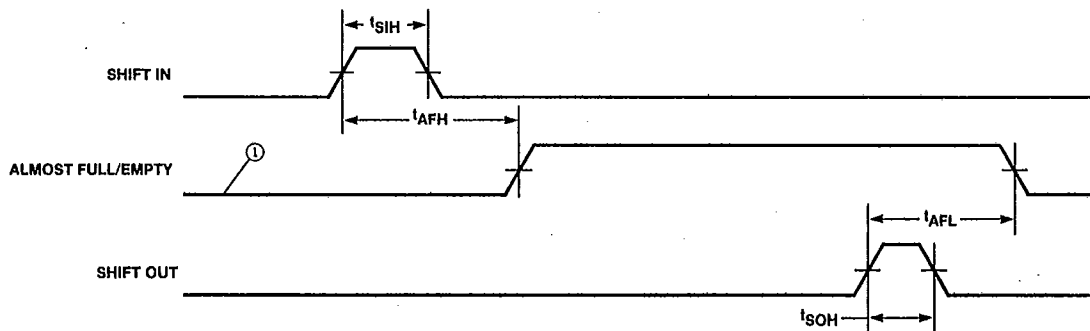


Figure 11. t_{AFH} , t_{AFL} Specifications

① FIFO contains 55 words (one short of almost full).

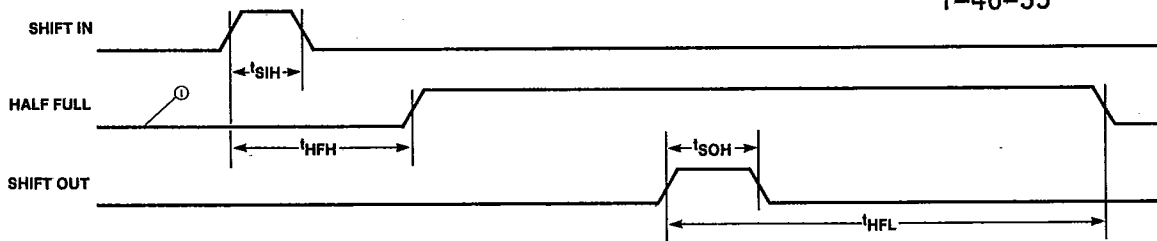
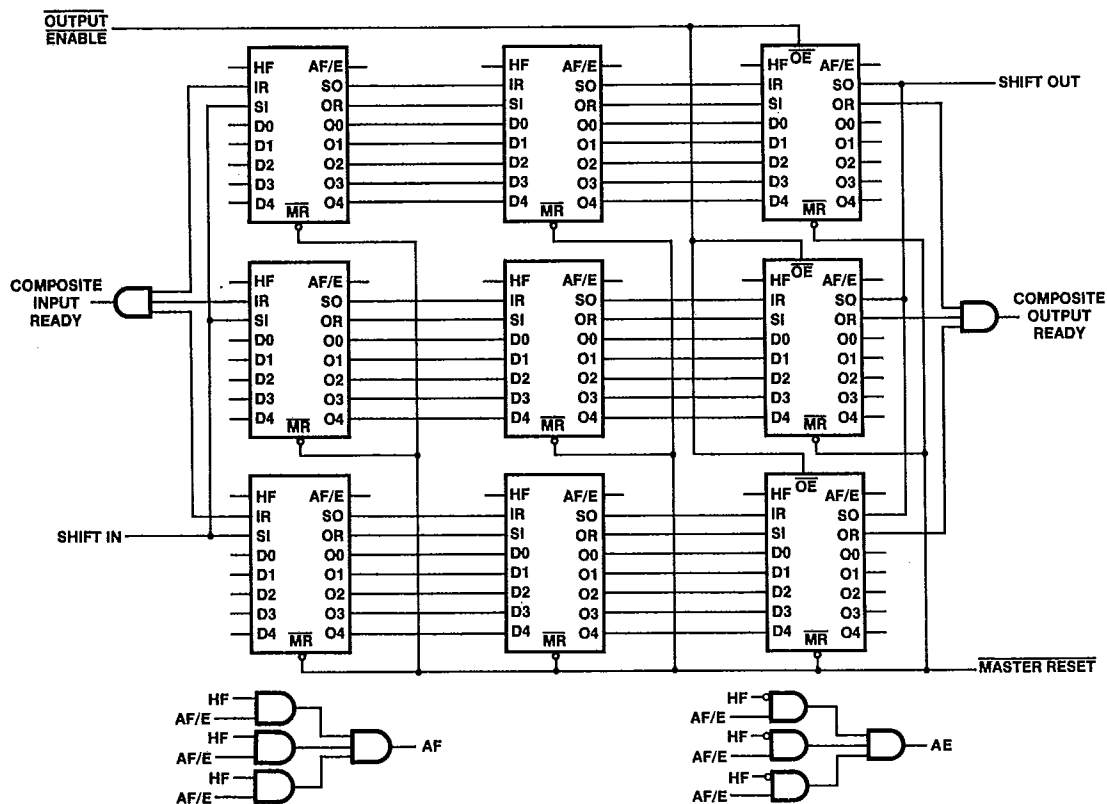


Figure 12. t_{HFL} , t_{HFH} Specifications

① FIFO contains 31 words (one short of half full).



Almost Full (AF) is eight words or less to FIFO full.
 Almost Empty (AE) is eight words or less to FIFO empty

Figure 13. 192x15 FIFO

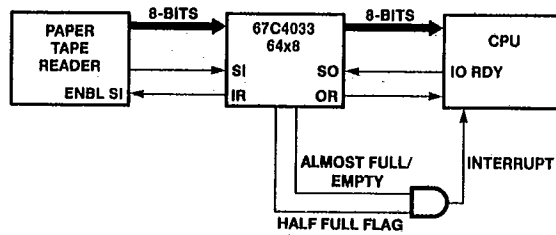
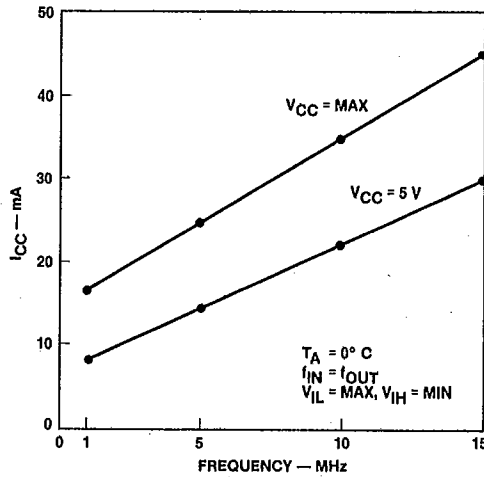


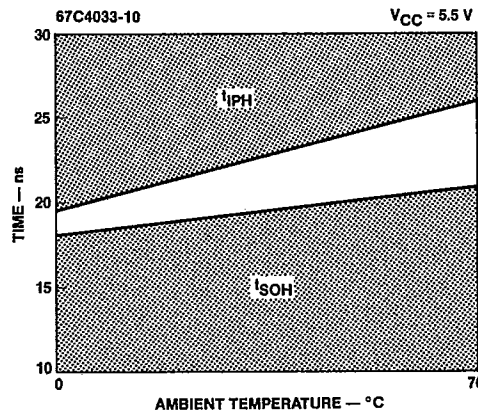
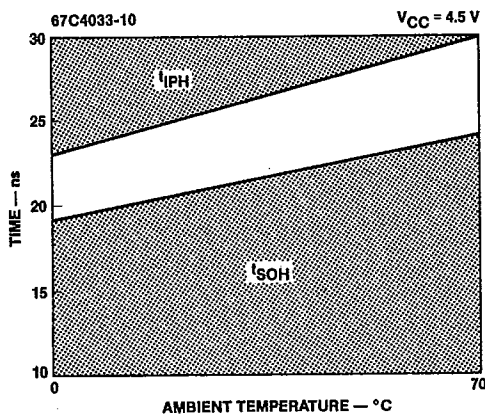
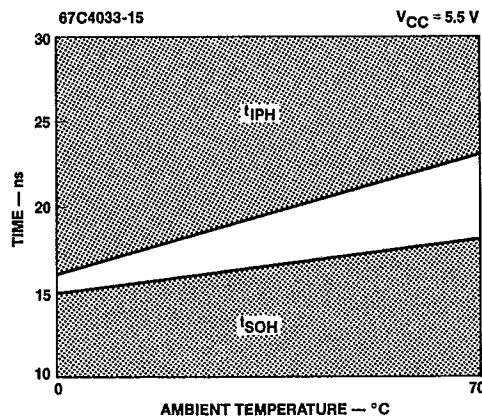
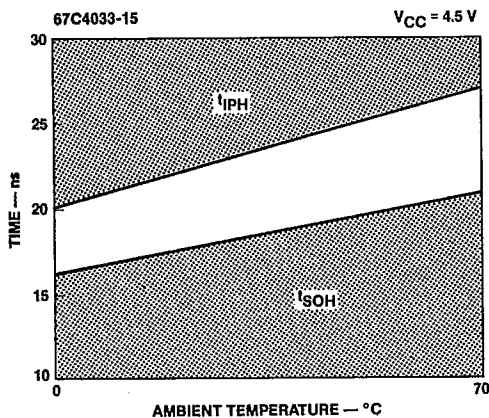
Figure 14. Application for 67C4033 "Slow and Steady Rate to Fast 'Blocked Rate' "

Note: Expanding the FIFOs in word width is done by ANDing the IR and OR as shown in Figure 13.

I_{CC} VS. FREQUENCY



Guaranteed Distribution of t_{PH} , t_{SOH} vs. Temperature (For Cascadability Only)



Guaranteed Distribution of t_{OPH} , t_{SIH} vs. Temperature (For Cascadability Only)

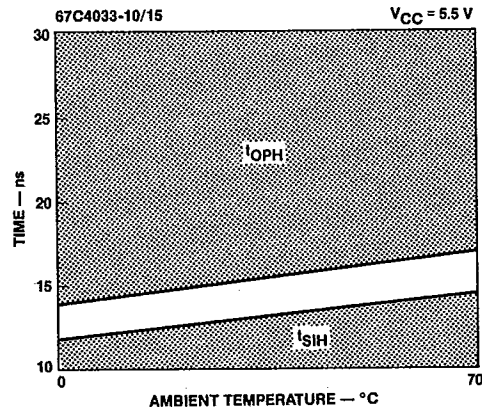
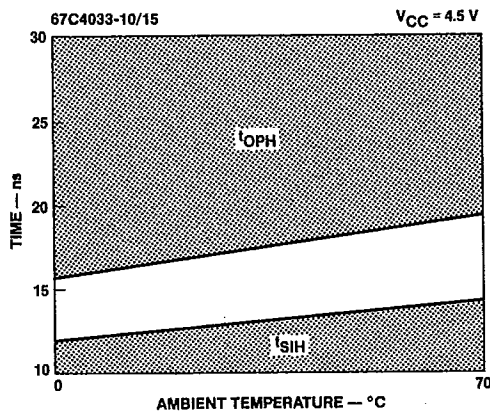


Figure B. Cascadability